

Features

- Trench/Fieldstop IGBT
- Low Switching Losses
- Standard package
- Copper Base Plate
- Solder Contact Technology
- Integrated NTC temperature sensor



Typical Applications

- Motor Drives
- Servo Drives
- Auxiliary Inverters

IGBT, Inverter

Maximum Rated Values						
Symbol	Item	Conditions	Rating	Unit		
IGBT						
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}C$	1200	V		
V_{GES}	Gate-emitter voltage	-	± 20	V		
I_C	Collector current,DC	$T_C=80^{\circ}C, T_{vj}=175^{\circ}C$	40	A		
I_{CRM}	Repetitive peak collector current	$t_p=1ms$	80	A		
P_{tot}	Total power dissipation	$T_C=25^{\circ}C, T_{vj}=175^{\circ}C$	250	W		
Characteristics Values						
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$	-	-	1	mA
I_{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$	-	-	100	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=0.8mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$	5.2	5.6	6.6	V
V_{CESat}	Collector-emitter saturation voltage	$I_C=40A$ $V_{GE}=15V$ $T_{vj}=25^{\circ}C$	-	2.23	-	
		$T_{vj}=125^{\circ}C$	-	-	-	
		$T_{vj}=150^{\circ}C$	-	-	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$	-	1.77	-	nF
C_{oes}	Output capacitance		-	0.17	-	
C_{res}	Reverse transfer capacitance		-	0.06	-	
Q_G	Gate charge	$V_{CC}=600V, I_C=25A$ $V_{GE}=-15...+15V, T_{vj}=25^{\circ}C$	-	0.24	-	μC
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$	-	-	-	Ω

$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$ $I_C=40A$ $V_{GE}=\pm 15V$ $R_{G(on)}=51\Omega$ $R_{G(off)}=51\Omega$	$T_{vj}=25^\circ C$	-	203	-	ns
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_r	Rise time		$T_{vj}=25^\circ C$	-	74	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^\circ C$	-	439	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_f	Fall time		$T_{vj}=25^\circ C$	-	219	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^\circ C$	-	10.1	-	mJ	
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^\circ C$	-	2.3	-		
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		
SC data	Short-circuit current	$V_{CC}=600V, V_{GE}\leq 15V, T_{vj}=125^\circ C$ $V_{CES}\leq 1200V, t_p\leq 10\mu s$	-	180	-	A	
R_{thJC}	Thermal resistance, junction to case	Per IGBT	-	-	0.6	K/W	
R_{thCH}	Thermal resistance, case to heatsink	Per IGBT $\lambda_{grease}=1W/(m\cdot K)$	-	0.295	-	K/W	
T_{vjop}	Temperature under switching conditions		-40		150	$^\circ C$	

Diode, Inverter
Maximum Rated Values

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^\circ C$	1200	V
I_F	Forward current, DC	$T_C=80^\circ C, T_{vj}=175^\circ C$	40	A
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	80	A
I^2t	I^2t -value	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	320	A^2s

Characteristic Values

			Min.	Typ.	Max.		
V_F	Continuous forward voltage	$I_F=40A$ $V_{GE}=0V$	$T_{vj}=25^\circ C$	-	2.21	-	V
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
I_{RM}	Peak reverse recovery current	$V_R=600V$ $I_F=40A$ $V_{GE}=-15V$	$T_{vj}=25^\circ C$	-	18	-	A
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_{rr}	Reverse recovery time		$T_{vj}=25^\circ C$	-	308	-	ns
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
Q_r	Recovered charge	$T_{vj}=25^\circ C$	-	2.59	-	μC	
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		

E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	0.92	-	mJ
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
R _{thJC}	Thermal resistance, junction to case	Per diode	-	-	-	0.95	K/W
T _{vjop}	Temperature under switching conditions			-40		150	°C

Diode, Rectifier

Maximum Rated Values							
Symbol	Item	Conditions		Rating			Unit
V _{RRM}	Repetitive peak reverse voltage	T _{vj} =25°C		1800			V
I _{FRMSM}	Maximum RMS forward current per chip	T _C =80°C		50			A
I _{RMSM}	Maximum RMS current at rectifier output	T _C =80°C		60			A
I _{FSM}	Surge forward current	t _p = 10 ms, T _{vj} = 150° C		350			A
I ² t	I ² t-value	t _p =10ms, T _{vj} =150°C		605			A ² s
Characteristic Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
V _F	Continuous forward voltage	I _F =40A V _{GE} =0V	T _{vj} =25°C	-	1.26	-	V
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
I _R	Reverse current	V _R =1800V	T _{vj} =25°C	-	-	10	uA
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
R _{thJC}	Thermal resistance, junction to case	Per diode	-	-	1	K/W	
T _{vjop}	Temperature under switching conditions			-40		150	°C

IGBT, Brake-Chopper

Maximum Rated Values							
Symbol	Item	Conditions		Values			Unit
V _{CES}	Collector-emitter voltage	T _{vj} =25°C		1200			V
V _{GES}	Gate-emitter voltage	-		±20			V
I _C	Collector current, DC	T _C =100°C, T _{vj} =175°C		15			A
I _{CRM}	Repetitive peak collector current	t _p =1ms		30			A
P _{tot}	Total power dissipation	T _C =25°C, T _{vj} =175°C		125			W
Characteristic Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector-emitter cut-off current	V _{CE} =1200V, V _{GE} =0V, T _{vj} =25°C		-	-	1	mA
I _{GES}	Gate leakage current	V _{CE} =0V, V _{GE} =20V, T _{vj} =25°C		-	-	100	nA
V _{GE(th)}	Gate-emitter threshold voltage	I _C =0.5mA, V _{CE} =V _{GE} , T _{vj} =25°C		5.7	6.2	6.7	V
V _{CESat}	Collector-emitter saturation voltage	I _C =15A V _{GE} =15V	T _{vj} =25°C	-	2.05	-	
			T _{vj} =125°C	-	-	-	

			$T_{vj}=150^{\circ}\text{C}$	-	-	-	
C_{ies}	Input capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}$ $f=1\text{MHz}, T_{vj}=25^{\circ}\text{C}$		-	1.19	-	nF
C_{oes}	Output capacitance			-	0.08	-	
C_{res}	Reverse transfer capacitance			-	0.04	-	
Q_G	Gate charge	$V_{CC}=600\text{V}, I_C=15\text{A}$ $V_{GE}=-15\dots+15\text{V}, T_{vj}=25^{\circ}\text{C}$		-	0.094	-	μC
R_g	Internal gate resistance	$T_{vj}=25^{\circ}\text{C}$		-	-	-	Ω
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{V}$ $I_C=15\text{A}$ $V_{GE}=\pm 15\text{V}$ $R_{G(on)}=51\Omega$ $R_{G(off)}=51\Omega$	$T_{vj}=25^{\circ}\text{C}$	-	124	-	ns
			$T_{vj}=125^{\circ}\text{C}$	-	-	-	
			$T_{vj}=150^{\circ}\text{C}$	-	-	-	
t_r	Rise time		$T_{vj}=25^{\circ}\text{C}$	-	148	-	
			$T_{vj}=125^{\circ}\text{C}$	-	-	-	
			$T_{vj}=150^{\circ}\text{C}$	-	-	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^{\circ}\text{C}$	-	173	-	
			$T_{vj}=125^{\circ}\text{C}$	-	-	-	
			$T_{vj}=150^{\circ}\text{C}$	-	-	-	
t_f	Fall time		$T_{vj}=25^{\circ}\text{C}$	-	299	-	
			$T_{vj}=125^{\circ}\text{C}$	-	-	-	
			$T_{vj}=150^{\circ}\text{C}$	-	-	-	
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^{\circ}\text{C}$	-	4	-	mJ	
		$T_{vj}=125^{\circ}\text{C}$	-	-	-		
		$T_{vj}=150^{\circ}\text{C}$	-	-	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^{\circ}\text{C}$	-	0.94	-		
		$T_{vj}=125^{\circ}\text{C}$	-	-	-		
		$T_{vj}=150^{\circ}\text{C}$	-	-	-		
SC data	Short-circuit current	$V_{CC}=600\text{V}, V_{GE}\leq 15\text{V}, T_{vj}=125^{\circ}\text{C}$ $V_{CES}\leq 1200\text{V}, t_p\leq 10\mu\text{s}$		-	60	-	A
R_{thJC}	Thermal resistance, junction to case	Per IGBT		-	-	1.2	K/W
T_{vjop}	Temperature under switching conditions			-40	-	150	$^{\circ}\text{C}$

Diode, Brake-Chopper
Maximum Rated Values

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^{\circ}\text{C}$	1200	V
I_F	Forward current, DC	$T_C=80^{\circ}\text{C}, T_{vj}=175^{\circ}\text{C}$	10	A
I_{FRM}	Repetitive peak forward current	$t_p=1\text{ms}$	20	A
I^2t	I^2t -value	$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=125^{\circ}\text{C}$	20	A^2s

Characteristic Values

			Min.	Typ.	Max.		
V_F	Continuous forward voltage	$I_F=10\text{A}$ $V_{GE}=0\text{V}$	$T_{vj}=25^{\circ}\text{C}$	-	2.05	-	V
			$T_{vj}=125^{\circ}\text{C}$	-	-	-	
			$T_{vj}=150^{\circ}\text{C}$	-	-	-	
I_{RM}	Peak reverse recovery current	$V_R=600\text{V}$ $I_F=15\text{A}$ $V_{GE}=-15\text{V}$	$T_{vj}=25^{\circ}\text{C}$	-	5.5	-	A
			$T_{vj}=125^{\circ}\text{C}$	-	-	-	
			$T_{vj}=150^{\circ}\text{C}$	-	-	-	

t _{rr}	Reverse recovery time		T _{vj} =25°C	-	942	-	ns
			T _{vj} =125°C	-	-	-	
Q _r	Recovered charge		T _{vj} =25°C	-	2.5	-	μC
			T _{vj} =125°C	-	-	-	
E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	0.88	-	mJ
			T _{vj} =125°C	-	-	-	
T _{vjop}	Temperature under switching conditions			-40		150	°C

Note:

IGBT electrical characteristics according to IEC 60747 – 9

Diode electrical characteristics according to IEC 60747 – 2

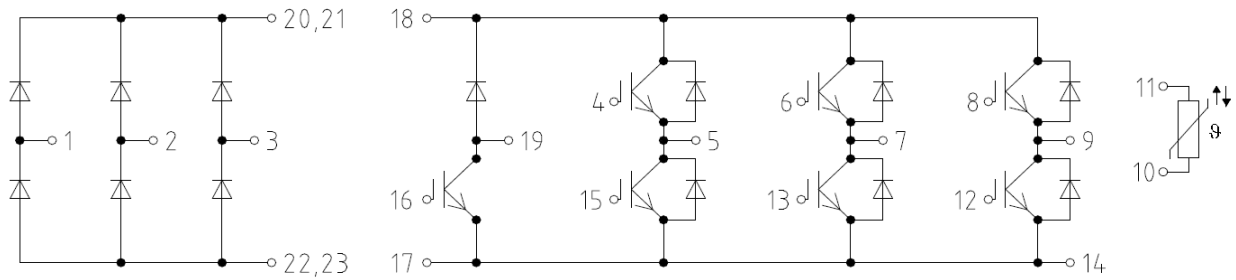
NTC Thermistor Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R ₂₅	Rated resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of resistance	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-constant	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$	-	3375	-	K
B _{25/80}	B-constant	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$	-	3411	-	
B _{25/100}	B-constant	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15K))]$	-	3433	-	

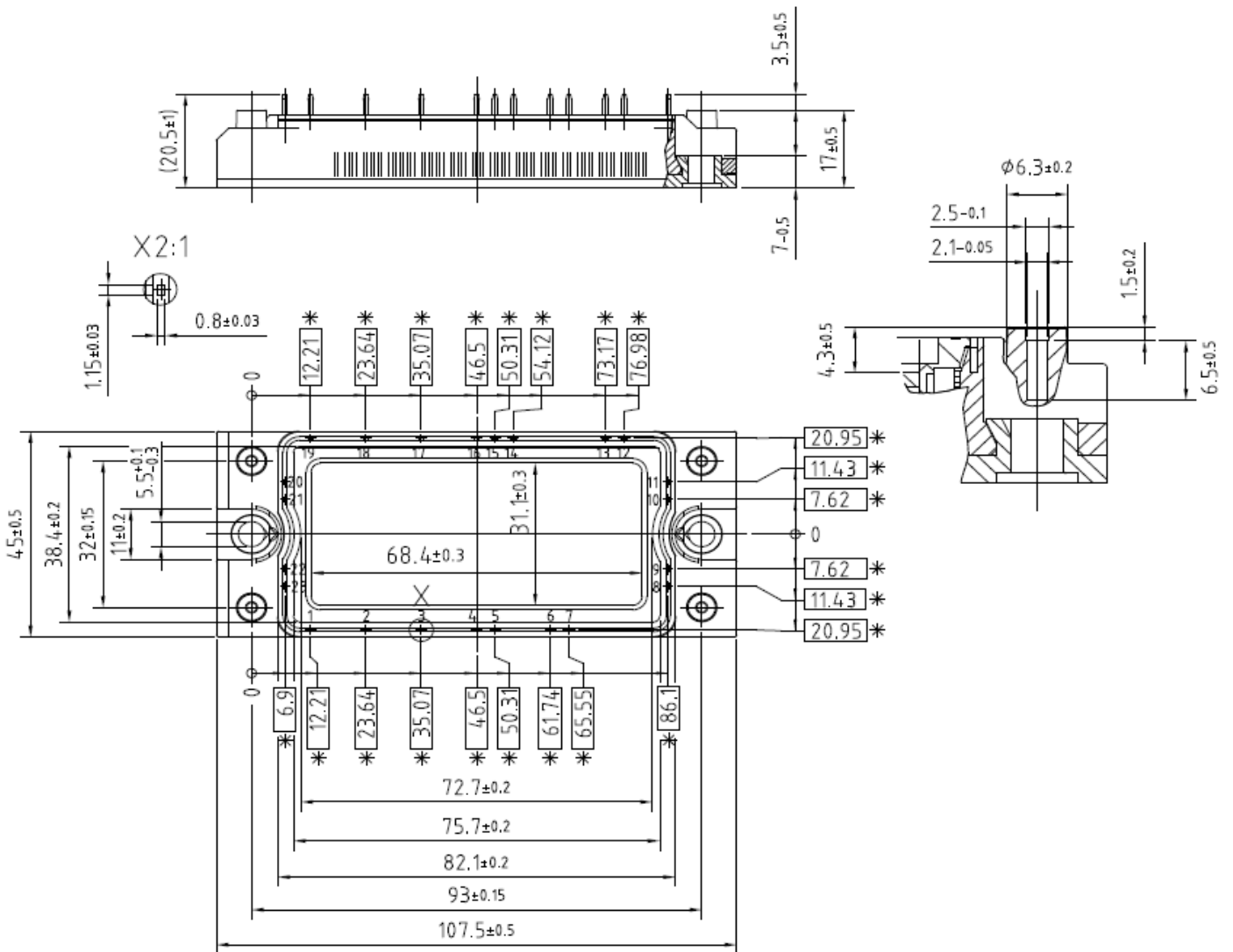
Module

Symbol	Item	Conditions	Rating			Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	2500			V
T _{vj max}	Maximum junction temperature	-	175			°C
T _{vj op}	Operating junction temperature	Continuous operationg(under switching)	-40~150			°C
T _{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
Ms	Mounting torque	Mounting to heat sink, M5 screw	3	-	6	Nm
ds	Creepage distance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	10	-	
da	Clearance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	7.5	-	
m	Weight	-	-	175	-	g

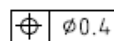
Circuit Diagram



Package Outlines



* = alle Maße mit einer Toleranz von
 * = all dimensions with tolerance of



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